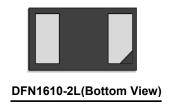


# **Uni-directional 5V High Capacitance TVS**

#### **Description**

The PTVSHC2EN5VU transient voltage suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. PTVSHC2EN5VU protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC2EN5VU is available in a DFN1610-2L package with working voltages of 5 volt.



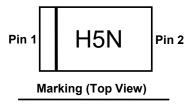
#### **Feature**

- $\rightarrow$  1600W Peak pulse power per line (t<sub>P</sub> = 8/20µs)
- DFN1610-2L package
- > Response time is typically < 1 ns
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
  ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 80A (5/50ns)
  IEC 61000-4-5 (Lightning) 130A (8/20us)

# Pin 1 Circuit Diagram

#### **Applications**

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

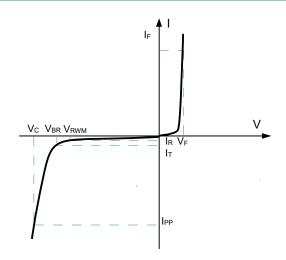


#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- ➤ Pin flatness:≤3mil
- Device meets MSL 3 requirements

#### **Electronics Parameter**

Symbol	Parameter	
V <sub>RWM</sub>	Peak Reverse Working Voltage	
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>	
$V_{BR}$	Breakdown Voltage @ I⊤	
I <sub>T</sub>	Test Current	
lpp	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P <sub>PP</sub>	Peak Pulse Power	
Сл	Junction Capacitance	
IF	Forward Current	
VF	Forward Voltage @ I <sub>F</sub>	



# Electrical characteristics per line@25℃( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				5	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> =1mA	6	7	8	V
Reverse Leakage Current	IR	V <sub>RWM</sub> =5V			2	μA
Clamping Voltage	Vc	I <sub>PP</sub> =20A t <sub>P</sub> = 8/20μs		8	9	V
Clamping Voltage	Vc	I <sub>PP</sub> =70A t <sub>P</sub> = 8/20μs		10	11	V
Clamping Voltage	Vc	I <sub>PP</sub> =130A t <sub>P</sub> = 8/20μs		12.5	14	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz	800	1000	1200	pF

## Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>P</sub> = 8/20µS )	P <sub>pp</sub>	1600	W
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	℃

## Typical Characteristics

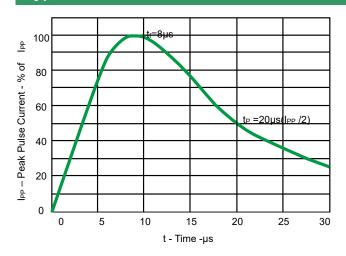


Fig 1.Pulse Waveform

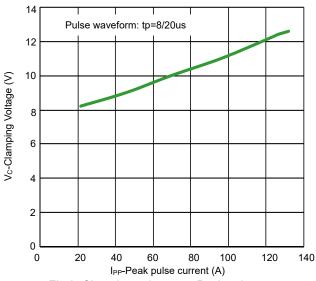


Fig 3. Clamping voltage vs. Peak pulse current

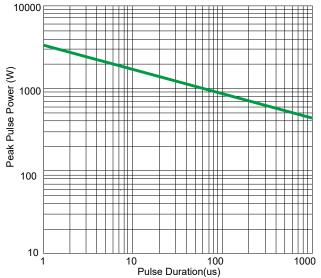


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

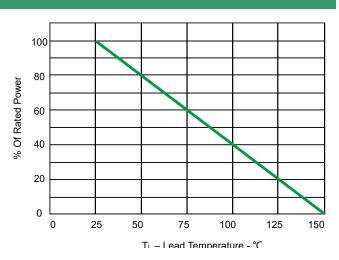


Fig 2.Power Derating Curve

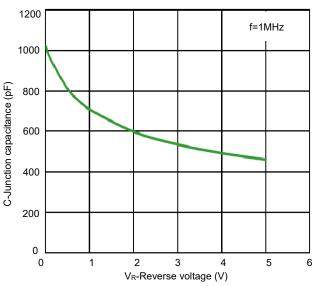
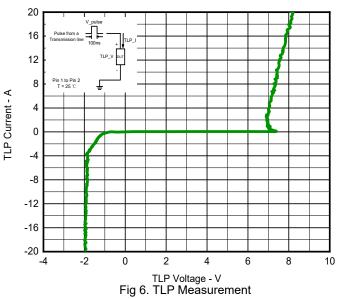
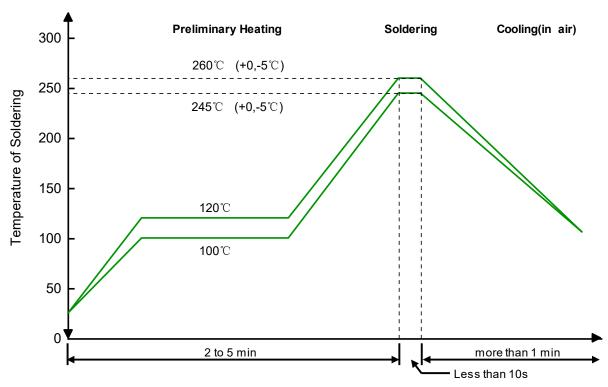


Fig 4. Capacitance vs. Reveres voltage



#### **Solder Reflow Recommendation**



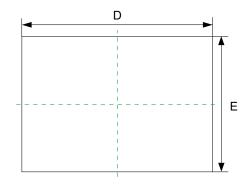
Remark: Pb free for 260°C; Pb for 245°C.

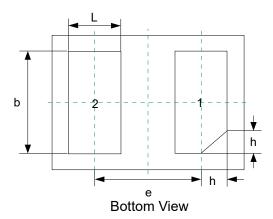
#### **PCB Design**

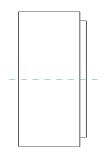
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

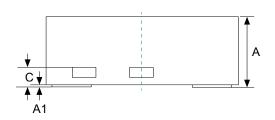
- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

# Product dimension (DFN1610-2L)

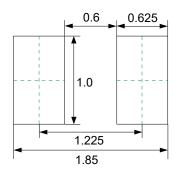








Dim	Millimeters		
	MIN	MAX	
Α	0.40	0.60	
A1	-	0.05	
b	0.75	0.85	
С	0.10	0.20	
D	1.55	1.65	
е	1.10BSC		
E	0.95	1.05	
L	0.35	0.45	
h	0.15	0.25	



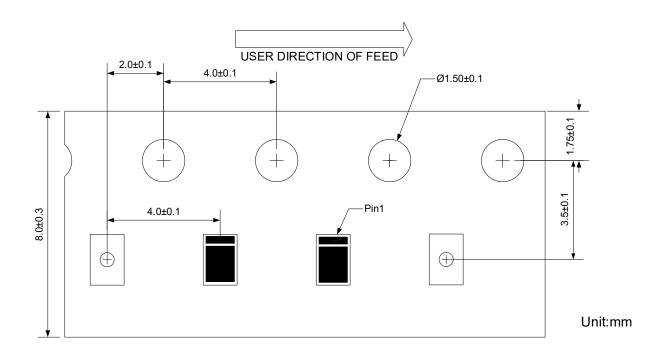
Recommended Soldering Pad

Unit:mm

## Ordering information

Device	Package	Reel	Shipping
PTVSHC2EN5VU	DFN1610-2L (Pb-Free)	7"	3000 / Tape & Reel

# Load with information



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